Feng Pan

List of Publications by Year
in descending order

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396 papers	15,476 citations	15504 65 h-index	25787 108 g-index
402 all docs	402 docs citations	402 times ranked	13298 citing authors

#	Article	IF	Citations
1	Interfaceâ€Enhanced Ferromagnetism with Longâ€Distance Effect in van der Waals Semiconductor. Advanced Functional Materials, 2022, 32, 2108953.	14.9	13
2	SAW Filters With Excellent Temperature Stability and High Power Handling Using LiTaO₃/SiC Bonded Wafers. Journal of Microelectromechanical Systems, 2022, 31, 186-193.	2.5	10
3	Memristive Behaviors Dominated by Reversible Nucleation Dynamics of Phaseâ€Change Nanoclusters. Small, 2022, , 2105070.	10.0	3
4	An overview of SrRuO₃-based heterostructures for spintronic and topological phenomena. Journal Physics D: Applied Physics, 2022, 55, 233001.	2.8	15
5	Antiferromagnetic Magnon Drag Effect and Giant Onâ€“Off Ratio in a Vertical Device. Advanced Quantum Technologies, 2022, 5, .	3.9	2
6	Controllable Generation of Antiferromagnetic Skyrmions in Synthetic Antiferromagnets with Thermal Effect. Advanced Functional Materials, 2022, 32, .	14.9	16
7	Investigation of Temperature-Dependent Magnetic Properties and Coefficient of Thermal Expansion in Invar Alloys. Materials, 2022, 15, 1504.	2.9	2
8	Efficient orbital torque in polycrystalline <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mrow><mml:mi>ferromagnetic</mml:mi><mml:mtext>â^'</mml:mtext><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> stacks: Theory and experiment. Physical Review B, 2022, 105, .	3.2	14
9	Polarization Evolution in Nanometer-Thick PbZrO₃ Films: Implications for Energy Storage and Pyroelectric Sensors. ACS Applied Nano Materials, 2022, 5, 6083-6088.	5.0	5
10	Tunable Spin Hall Magnetoresistance in All-Antiferromagnetic Heterostructures. Chinese Physics Letters, 2022, 39, 047502.	3.3	3
11	High Chern number quantum anomalous Hall effect tunable by stacking order in van der Waals topological insulators. Physical Review B, 2022, 105, .	3.2	16
12	Observation of Spin Splitting Torque in a Collinear Antiferromagnet <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>RuO</mml:mi></mml:mrow><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> Physical Review Letters, 2022, 128, .	7.8	68
13	Piezoelectric Strain-Controlled Magnon Spin Current Transport in an Antiferromagnet. Nano Letters, 2022, 22, 4646-4653.	9.1	6
14	A Low-Loss Wideband SAW Filter With Low Drift Using Multilayered Structure. IEEE Electron Device Letters, 2022, 43, 1371-1374.	3.9	8
15	Over GHz bandwidth SAW filter based on 32Â° Y-X LN/SiO2/poly-Si/Si heterostructure with multilayer electrode modulation. Applied Physics Letters, 2022, 120, .	3.3	22
16	Orthogonal interlayer coupling in an all-antiferromagnetic junction. Nature Communications, 2022, 13, .	12.8	7
17	Spin-orbit torques: Materials, mechanisms, performances, and potential applications. Progress in Materials Science, 2021, 118, 100761.	32.8	127
18	Evolution of domain structure in Fe3GeTe2 *. Chinese Physics B, 2021, 30, 027505.	1.4	7

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19	Observation of the antiferromagnetic spin Hall effect. Nature Materials, 2021, 20, 800-804.	27.5	113
20	Study of spin mixing conductance of single oriented Pt in Pt/Ni81Fe19 heterostructure by spin pumping. AIP Advances, 2021, 11, 035211.	1.3	2
21	Wideband and Low-Loss Surface Acoustic Wave Filter Based on 15Â° YX-LiNbOâ‚ƒ/SiOâ‚‚/Si Structure. IEEE Electron Device Letters, 2021, 42, 438-441.	3.9	73
22	Emerging opportunities for voltage-driven magneto-ionic control in ferroic heterostructures. APL Materials, 2021, 9, .	5.1	22
23	Reducing Dzyaloshinskii-Moriya interaction and field-free spin-orbit torque switching in synthetic antiferromagnets. Nature Communications, 2021, 12, 3113.	12.8	47
24	Insight into interlayer magnetic coupling in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mn>1</mml:mn><mml:mi>T</mml:mi></mml:math> -type transition metal dichalcogenides based on the stacking of nonmagnetic atoms. Physical Review B, 2021, 103, .	3.2	7
25	Observation of negative capacitance in antiferroelectric PbZrO3 Films. Nature Communications, 2021, 12, 4215.	12.8	22
26	Enhanced Coupling Coefficient in Dual-Mode ZnO/SiC Surface Acoustic Wave Devices with Partially Etched Piezoelectric Layer. Applied Sciences (Switzerland), 2021, 11, 6383.	2.5	10
27	Plasma Etchingâ€Assisted Perpendicular Magnetic Anisotropy. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100368.	1.8	1
28	Near 30% fractional bandwidth surface acoustic wave filters with novel electrode configuration. Progress in Natural Science: Materials International, 2021, 31, 852-857.	4.4	9
29	Designing Allâ€Inorganic EuOâ€Sensitized TiO 2 Solar Cell from 4fâ€3d Composite Bandgap Structure. Advanced Theory and Simulations, 2021, 4, 2100235.	2.8	2
30	Structure with thin SiOx/SiNx bilayer and Al electrodes for high-frequency, large-coupling, and low-cost surface acoustic wave devices. Ultrasonics, 2021, 115, 106460.	3.9	6
31	Spinâ€Dependent Charge Transport in 1D Chiral Hybrid Leadâ€Bromide Perovskite with High Stability. Advanced Functional Materials, 2021, 31, 2104605.	14.9	44
32	Temperatureâ€Dependent Terahertz Emission from Co/Mn 2 Au Spintronic Bilayers. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100290.	2.4	10
33	A Multilayered Structure for Packageless Acoustic- Wave Devices With Ultra-Small Sizes. Journal of Microelectromechanical Systems, 2021, 30, 589-596.	2.5	7
34	High-Performance Surface Acoustic Wave Devices Using LiNbO₃/SiO₂/SiC Multilayered Substrates. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 3693-3705.	4.6	67
35	Control of spin-orbit torques through magnetic symmetry in differently oriented noncollinear antiferromagnetic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Mn</mml:mi><mml:mn>3</mml:mn></mml:mn></mml:mi></mml:msub></mml:mrow></mml:math> Physical Review B, 2021, 104, .	3.2	18
36	Nobleâ€Metalâ€Assisted Fast Interfacial Oxygen Migration with Topotactic Phase Transition in Perovskite Oxides. Advanced Functional Materials, 2021, 31, 2106765.	14.9	18

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37	Highly Efficient Spinâ€Filtering Transport in Chiral Hybrid Copper Halides. Angewandte Chemie, 2021, 133, 23770.	2.0	1
38	Highly Efficient Spinâ€Filtering Transport in Chiral Hybrid Copper Halides. Angewandte Chemie - International Edition, 2021, 60, 23578-23583.	13.8	43
39	Systematical Study of the Basic Properties of Surface Acoustic Wave Devices Based on ZnO and GaN Multilayers. Electronics (Switzerland), 2021, 10, 23.	3.1	15
40	Facilitating room-temperature oxygen ion migration via Coâ€“O bond activation in cobaltite films. Nanoscale, 2021, 13, 18256-18266.	5.6	8
41	Ultra-Wideband Surface Acoustic Wave Filters Based on the Cu/LiNbO₃/SiO₂/SiC Structure. , 2021, , .		3
42	Basic Logic Operations Achieved in a Single 2D WSe2 Transistor by Surface-Charge-Transfer Doping. ACS Applied Electronic Materials, 2021, 3, 5059-5065.	4.3	1
43	Terahertz pulse-induced NÃ©el vector switching in Î±-Fe2O3/Pt heterostructures. Applied Physics Letters, 2021, 119, 212401.	3.3	7
44	Cluster magnetic octupole induced out-of-plane spin polarization in antiperovskite antiferromagnet. Nature Communications, 2021, 12, 6524.	12.8	34
45	Bias-dependent tunneling anisotropic magnetoresistance in antiferromagnetic Pd-doped FeRh-based junctions. Applied Physics Letters, 2021, 119, .	3.3	2
46	Charge-magnon conversion at the topological insulator/antiferromagnetic insulator interface. Physical Review B, 2020, 102, .	3.2	2
47	Design of a Controllable Redoxâ€Diffusive Threshold Switching Memristor. Advanced Electronic Materials, 2020, 6, 2000695.	5.1	43
48	3D Layout of Interdigital Transducers for High Frequency Surface Acoustic Wave Devices. IEEE Access, 2020, 8, 123262-123271.	4.2	16
49	Formation and annihilation of multi-antiskyrmion defects during skyrmion nucleation. Journal of Applied Physics, 2020, 128, .	2.5	1
50	Tunable spinâ€“orbit torque switching in antiferromagnetically coupled CoFeB/Ta/CoFeB. Applied Physics Letters, 2020, 117, 212403.	3.3	10
51	Ultrafast electron transport in metallic antiferromagnetic Mn2Au thin films probed by terahertz spectroscopy. Physical Review B, 2020, 102, .	3.2	4
52	Enhanced Performance of ZnO/SiO₂/Al₂O₃ Surface Acoustic Wave Devices with Embedded Electrodes. ACS Applied Materials & Interfaces, 2020, 12, 42378-42385.	8.0	17
53	Size-dependent anomalous Hall effect in noncollinear antiferromagnetic Mn3Sn films. Applied Physics Letters, 2020, 117, .	3.3	22
54	Exchange Bias in Antiferromagnetic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mi>Mn</mml:mi><mml:mn>3</mml:mn></mml:msub><mml:mi>Sn</mml:mi></mml:math> Monolayer Films. Physical Review Applied, 2020, 14, .	3.8	7

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55	Functional antiferromagnets for potential applications on high-density storage and high frequency. Journal of Applied Physics, 2020, 128, .	2.5	18
56	Room temperature anomalous Hall effect in antiferromagnetic Mn3SnN films. Applied Physics Letters, 2020, 117, .	3.3	20
57	Performance Improvement of Conductive Bridging Random Access Memory by Electrode Alloying. Journal of Physical Chemistry C, 2020, 124, 11438-11443.	3.1	9
58	Cluster-Type Filaments Induced by Doping in Low-Operation-Current Conductive Bridge Random Access Memory. ACS Applied Materials & Interfaces, 2020, 12, 29481-29486.	8.0	4
59	Current-induced magnetization switching in a CoTb amorphous single layer. Physical Review B, 2020, 101, .	3.2	59
60	Current-Induced In-Plane Magnetization Switching in a Biaxial Ferrimagnetic Insulator. Physical Review Applied, 2020, 13, .	3.8	14
61	Magnetic field direction dependence of topological Hall effect like features in synthetic ferromagnetic and antiferromagnetic multilayers. Applied Physics Letters, 2020, 116, 242403.	3.3	9
62	High-frequency and high-temperature stable surface acoustic wave devices on ZnO/SiO2/SiC structure. Journal Physics D: Applied Physics, 2020, 53, 305102.	2.8	12
63	Highâ€Performance Optoelectronics: Lateral 2D WSe₂ pâ€“n Homojunction Formed by Efficient Chargeâ€Carrierâ€Type Modulation for Highâ€Performance Optoelectronics (Adv. Mater. 9/2020). Advanced Materials, 2020, 32, 2070067.	21.0	2
64	Interfacial Control of Ferromagnetism in Ultrathin SrRuO₃ Films Sandwiched between Ferroelectric BaTiO₃ Layers. ACS Applied Materials & Interfaces, 2020, 12, 6707-6715.	8.0	16
65	Lateral 2D WSe₂ pâ€“n Homojunction Formed by Efficient Chargeâ€Carrierâ€Type Modulation for Highâ€Performance Optoelectronics. Advanced Materials, 2020, 32, e1906499.	21.0	103
66	Implementing a Type of Synaptic Coupling between Excitatory and Inhibitory Cells by Using Pt/Poly(3,4-ethylenedioxythiophene):Polystyrenesulfonate/HfO_x/Pt Memristive Structure. Journal of Physical Chemistry C, 2020, 124, 4843-4851.	3.1	2
67	Realization of Isolated and High-Density Skyrmions at Room Temperature in Uncompensated Synthetic Antiferromagnets. Nano Letters, 2020, 20, 3299-3305.	9.1	42
68	A comparative study of spin Hall magnetoresistance in Fe2O3-based systems. Journal of Applied Physics, 2020, 127, .	2.5	10
69	Orientation control of oxygen vacancy channels in brownmillerite <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>SrFe</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mrow><mml:mn>2.5</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>. Physical Review Materials, 2020, 4, .	2.4	13
70	Interfacial oxygen-octahedral-tilting-driven electrically tunable topological Hall effect in ultrathin SrRuO₃ films. Journal Physics D: Applied Physics, 2019, 52, 404001.	2.8	51
71	Electric field control of NÃ©el spinâ€“orbit torque in an antiferromagnet. Nature Materials, 2019, 18, 931-935.	27.5	132
72	Tuning the magnetotransport behavior of topological insulator with a transition-metal oxide layer. Journal of Physics Condensed Matter, 2019, 31, 405001.	1.8	2

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73	Electric and Light Dual-Gate Tunable MoS₂ Memtransistor. ACS Applied Materials & Interfaces, 2019, 11, 43344-43350.	8.0	51
74	Orientation-dependent THz emission in non-collinear antiferromagnetic Mn3Sn and Mn3Sn-based heterostructures. Applied Physics Letters, 2019, 115, .	3.3	25
75	Simultaneous detection of the spin Hall magnetoresistance and Joule heating-induced spin Seebeck effect in Gd3Fe5O12/Pt bilayers. Journal of Applied Physics, 2019, 126, .	2.5	7
76	Strong magnetoresistance modulation by Ir insertion in a Ta/Ir/CoFeB trilayer. Physical Review B, 2019, 100, .	3.2	6
77	Magnetic field direction dependent magnetization reversal in synthetic antiferromagnets. Applied Physics Letters, 2019, 115, .	3.3	12
78	Electric Field Control of Phase Transition and Tunable Resistive Switching in SrFeO_{2.5}. ACS Applied Materials & Interfaces, 2019, 11, 6581-6588.	8.0	45
79	Modulating metallic conductive filaments via bilayer oxides in resistive switching memory. Applied Physics Letters, 2019, 114, 193502.	3.3	37
80	From Fieldlike Torque to Antidamping Torque in Antiferromagnetic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mi>Mn</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:mi>Au</mml:mi></mml:math>. Physical Review Applied, 2019, 11, .	3.8	36
81	Oxygen-Valve Formed in Cobaltite-Based Heterostructures by Ionic Liquid and Ferroelectric Dual-Gating. ACS Applied Materials & Interfaces, 2019, 11, 19584-19595.	8.0	30
82	Spin valve effect induced by spin-orbit torque switching. Applied Physics Letters, 2019, 114, .	3.3	4
83	Nonvolatile Memory: Performanceâ€Enhancing Selector via Symmetrical Multilayer Design (Adv. Funct.) Tj ETQq1 1 0.784314 rgBT /Ove	14.9	7
84	High-frequency V-doped ZnO/SiC surface acoustic wave devices with enhanced electromechanical coupling coefficient. Applied Physics Letters, 2019, 114, .	3.3	21
85	The effect of modulated matrix microstructure on the deformation behavior in SiC /Ti17 composites. Materials Letters, 2019, 242, 123-126.	2.6	6
86	Anomalous Hall Effectâ€“Like Behavior with Inâ€Plane Magnetic Field in Noncollinear Antiferromagnetic Mn₃Sn Films. Advanced Electronic Materials, 2019, 5, 1800818.	5.1	56
87	Electrical Control of Anisotropic Ferromagnetic Domains During Antiferromagnetic-Ferromagnetic Phase Transition. Physical Review Applied, 2019, 11, .	3.8	4
88	Phase-change nanoclusters embedded in a memristor for simulating synaptic learning. Nanoscale, 2019, 11, 5684-5692.	5.6	25
89	Self-Modulating Interfacial Cation Migration Induced Threshold Switching in Bilayer Oxide Memristive Device. Journal of Physical Chemistry C, 2019, 123, 878-885.	3.1	14
90	Simulation of temperature compensated waveguiding layer acoustic wave devices. Journal Physics D: Applied Physics, 2019, 52, 075105.	2.8	7

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91	High-Frequency Surface Acoustic Wave Devices Based on ZnO/SiC Layered Structure. IEEE Electron Device Letters, 2019, 40, 103-106.	3.9	45
92	Performanceâ€Enhancing Selector via Symmetrical Multilayer Design. Advanced Functional Materials, 2019, 29, 1808376.	14.9	56
93	Behavior of Al/Cu/Ti electrodes in surface acoustic wave filter at high power. Current Applied Physics, 2019, 19, 363-369.	2.4	6
94	Facile access to shape-controlled growth of WS ₂ monolayer via environment-friendly method. 2D Materials, 2019, 6, 015007.	4.4	18
95	Grain Size-Dependent Mechanical Properties of a High-Manganese Austenitic Steel. Acta Metallurgica Sinica (English Letters), 2019, 32, 746-754.	2.9	30
96	Enhanced power durability of surface acoustic wave filter with Al/Ti/Cu/Ti electrodes. Journal of Alloys and Compounds, 2018, 740, 222-228.	5.5	10
97	Competition between Metallic and Vacancy Defect Conductive Filaments in a CH₃NH₃PbI₃-Based Memory Device. Journal of Physical Chemistry C, 2018, 122, 6431-6436.	3.1	115
98	Microstructure and interfacial strength of SiC fiber-reinforced Ti17 alloy composites with different consolidation temperatures. Rare Metals, 2018, 37, 759-768.	7.1	13
99	Controllable oxygen vacancies, orbital occupancy and magnetic ordering in SrCoO 3â^Î´ films. Journal of Magnetism and Magnetic Materials, 2018, 454, 228-236.	2.3	13
100	Texture-enhanced Al-Cu electrodes on ultrathin Ti buffer layers for high-power durable 2.6 GHz SAW filters. AIP Advances, 2018, 8, 045212.	1.3	11
101	Improving Unipolar Resistive Switching Uniformity with Cone-Shaped Conducting Filaments and Its Logic-In-Memory Application. ACS Applied Materials & Interfaces, 2018, 10, 6453-6462.	8.0	68
102	How to manipulate magnetic states of antiferromagnets. Nanotechnology, 2018, 29, 112001.	2.6	79
103	Enhanced SAW characteristics of a-plane AlN epitaxial films using ZnO buffer layer. Journal of Materials Science: Materials in Electronics, 2018, 29, 3912-3919.	2.2	14
104	Characteristics of one-port surface acoustic wave resonator fabricated on ZnO/6H-SiC layered structure. Journal Physics D: Applied Physics, 2018, 51, 145305.	2.8	12
105	Evolution of microstructures and mechanical properties during solution treatment of a Tiâ€“Vâ€“Mo-containing highâ€manganese cryogenic steel. Materials Characterization, 2018, 135, 287-294.	4.4	26
106	Local Control of Exchange Bias by Resistive Switching. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1800446.	2.4	8
107	Control of Secondary Phases by Solution Treatment in a N-Alloyed High-Mn Cryogenic Steel. Acta Metallurgica Sinica (English Letters), 2018, 31, 1059-1072.	2.9	2
108	Antidamping-Torque-Induced Switching in Biaxial Antiferromagnetic Insulators. Physical Review Letters, 2018, 120, 207204.	7.8	246

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109	Strong Orientation-Dependent Spin-Orbit Torque in Thin Films of the Antiferromagnet <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>Mn</mml:mi></mml:mrow><mml:mn>2</mml:mn></mml:msub><mml:mi>Ir</mml:mi></mml:mrow></mml:math>. Physical Review Applied, 2018, 9, .	3.8	75
110	Adaptive Crystallite Kinetics in Homogenous Bilayer Oxide Memristor for Emulating Diverse Synaptic Plasticity. Advanced Functional Materials, 2018, 28, 1706927.	14.9	140
111	Light Tuning of the Resistance of NdNiO₃ Films With CoFe₂O₄ Capping. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1800186.	2.4	2
112	Improved resistance to electromigration and acoustomigration of Al interdigital transducers by Ni underlayer. Rare Metals, 2018, 37, 823-830.	7.1	10
113	Spin-orbit torque in a completely compensated synthetic antiferromagnet. Physical Review B, 2018, 97, .	3.2	73
114	Optimization of C/TiC duplex diffusion barrier coatings for SiC /Ti composites based on interfacial structure evolution exploration. Ceramics International, 2018, 44, 16528-16534.	4.8	4
115	Anomalous Hall effect in one monolayer cobalt with electrical manipulation. Journal of Alloys and Compounds, 2017, 696, 315-320.	5.5	3
116	Role of an ultrathin platinum seed layer in antiferromagnet-based perpendicular exchange coupling and its electrical manipulation. Journal of Magnetism and Magnetic Materials, 2017, 428, 431-436.	2.3	8
117	Quality-enhanced AlN epitaxial films grown on c-sapphire using ZnO buffer layer for SAW applications. Applied Surface Science, 2017, 402, 392-399.	6.1	37
118	Lateral transport properties of thermally excited magnons in yttrium iron garnet films. Applied Physics Letters, 2017, 110, .	3.3	22
119	A class of liquid anode for rechargeable batteries with ultralong cycle life. Nature Communications, 2017, 8, 14629.	12.8	71
120	Recent progress in voltage control of magnetism: Materials, mechanisms, and performance. Progress in Materials Science, 2017, 87, 33-82.	32.8	357
121	Spintronic materials and devices based on antiferromagnetic metals. Progress in Natural Science: Materials International, 2017, 27, 208-216.	4.4	31
122	Enhancement of yield strength by chromium/nitrogen alloying in high-manganese cryogenic steel. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2017, 698, 110-116.	5.6	41
123	Diverse Synaptic Plasticity Induced by the Interplay of Ionic Polarization and Doping at Salt-Doped Electrolyte/Semiconducting Polymer Interface. ACS Omega, 2017, 2, 746-754.	3.5	5
124	Spin-orbit torque in MgO/CoFeB/Ta/CoFeB/MgO symmetric structure with interlayer antiferromagnetic coupling. Physical Review B, 2017, 95, .	3.2	82
125	Metal-insulator-metal transition in NdNiO3 films capped by CoFe2O4. Applied Physics Letters, 2017, 110, .	3.3	12
126	Electric-Field Control of Oxygen Vacancies and Magnetic Phase Transition in a Cobaltite/Manganite Bilayer. Physical Review Applied, 2017, 8, .	3.8	32

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127	Sputtering power dependence of structure and photoluminescence of ZnO on 6Hâ€“SiC. Journal of Materials Science: Materials in Electronics, 2017, 28, 17881-17888.	2.2	5
128	Spinâ€“orbit torque switching in MgO/CoFeB/Ta/CoFeB/MgO heterostructures with a critical current density of 10⁵ A/cm². Japanese Journal of Applied Physics, 2017, 56, 100303.	1.5	4
129	Guiding the Growth of a Conductive Filament by Nanoindentation To Improve Resistive Switching. ACS Applied Materials & Interfaces, 2017, 9, 34064-34070.	8.0	106
130	Tunneling anisotropic magnetoresistance driven by magnetic phase transition. Nature Communications, 2017, 8, 449.	12.8	49
131	Hall detection of anisotropic domain walls during magnetic phase transition. Journal Physics D: Applied Physics, 2017, 50, 505004.	2.8	5
132	Photonâ€Gated Spin Transistor. Advanced Materials, 2017, 29, 1604052.	21.0	12
133	Chemical modulation of electronic structure at the excited state. Physical Review B, 2017, 96, .	3.2	1
134	Electrical control of antiferromagnetic metal up to 15 nm. Science China: Physics, Mechanics and Astronomy, 2016, 59, 1.	5.1	8
135	Manipulation of Electric Field Effect by Orbital Switch. Advanced Functional Materials, 2016, 26, 753-759.	14.9	49
136	Sliding threshold of spikeâ€rate dependent plasticity of a semiconducting polymer/electrolyte cell. Journal of Polymer Science, Part B: Polymer Physics, 2016, 54, 2412-2417.	2.1	3
137	Simulation of synaptic short-term plasticity using Ba(CF3SO3)2-doped polyethylene oxide electrolyte film. Scientific Reports, 2016, 6, 18915.	3.3	13
138	Unipolar resistive switching with forming-free and self-rectifying effects in Cu/HfO2/n-Si devices. AIP Advances, 2016, 6, .	1.3	19
139	Restoring the magnetism of ultrathin <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>LaMn</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> films by surface symmetry engineering. Physical Review B, 2016, 94, .	3.2	11
140	Electrochemical control of the phase transition of ultrathin FeRh films. Applied Physics Letters, 2016, 108, .	3.3	27
141	Strong Electrical Manipulation of Spinâ€“Orbit Torque in Ferromagnetic Heterostructures. Advanced Electronic Materials, 2016, 2, 1600219.	5.1	37
142	Insight into the antiferromagnetic structure manipulated by electronic reconstruction. Physical Review B, 2016, 94, .	3.2	16
143	Vertical spin Hall magnetoresistance in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi mathvariant="normal">T</mml:mi><mml:msub><mml:mi mathvariant="normal">a</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow><mml:mi mathvariant="normal">P</mml:mi><mml:msub><mml:mi mathvariant="normal">t</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:mrow><mml:mo>/</mml:mo><mml:mi>YIG</mml:mi></mml:mrow>	3.2	6
144	Designing room-temperature multiferroic materials in a single-phase solid-solution film. Journal Physics D: Applied Physics, 2016, 49, 365001.	2.8	3

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145	Optical control of magnetism in manganite films. Physical Review B, 2016, 93, .	3.2	10
146	Manipulating the metal-to-insulator transition of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>NdNi</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>films by orbital polarization. Physical Review B, 2016, 93, .	3.2	16
147	Electrical control of antiferromagnetic metals. , 2016, , .		0
148	Spin-Hall-Effect-Assisted Electroresistance in Antiferromagnets via 105â€‰A/cm2 dc Current. Scientific Reports, 2016, 6, 31966.	3.3	5
149	Realisation of all 16 Boolean logic functions in a single magnetoresistance memory cell. Nanoscale, 2016, 8, 12819-12825.	5.6	23
150	Electrical control of magnetism in oxides. Chinese Physics B, 2016, 25, 067502.	1.4	24
151	Influence of film composition on the transition temperature of FeRh films. Journal of Crystal Growth, 2016, 438, 19-24.	1.5	25
152	Role of Oxygen Ion Migration in the Electrical Control of Magnetism in Pt/Co/Ni/HfO₂ Films. Journal of Physical Chemistry C, 2016, 120, 1633-1639.	3.1	41
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